

Amendments to the Specification

Paragarph at page 23, line 24 to page 24, line 6:

In the case of the n-electrode, if the work function of the n-electrode is lower than the conduction band edge energy of the ambipolar inorganic semiconductor, a combination is formed which does not create the barrier between them. In the case of the p-electrode, if the work function of the p-electrode is higher than the ~~conduction~~ valence band edge energy of the ambipolar inorganic semiconductor, a combination is formed which does not create the barrier between them. When a junction with the ambipolar inorganic semiconductor is created, a material must be selected and a process must be designed so that an unintended barrier is not formed, for example, by inducing a chemical reaction.